

# 50 V, 170 mA dual P-channel Trench MOSFET Rev. 1 — 19 May 2011

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

### 1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 1 kV
- AEC-Q101 qualified
- High-side loadswitch
- Switching circuits

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C	-	-	-50	V
V <sub>GS</sub>	gate-source voltage		-20	-	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = -10 V; $T_{amb}$ = 25 °C	<u>[1]</u> _	-	-170	mA
Static cha	racteristics (per transisto	or)				
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = -10 \ V; \ I_D = -100 \ mA; \\ T_j = 25 \ ^\circ C \end{array}$	-	4.5	7.5	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		24 - 22
2	G1	gate 1		
3	D2	drain 2		
4	S2	source 2	0	G1 + F F F G2
5	G2	gate 2		
6	D1	drain 1	SOT666 (SOT666)	S1 S2 sym147

## 3. Ordering information

Table 3. Or	dering information		
Type number	Package		
	Name	Description	Version
BSS84AKV	SOT666	plastic surface-mounted package; 6 leads	SOT666

### 4. Marking

Table 4.	Marking codes	
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Type number	Marking code <sup>[1]</sup>
BSS84AKV	EG

[1] % = placeholder for manufacturing site code

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transi	istor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-50	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-170	mA
		$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$	<u>[1]</u>	-	-110	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-0.7	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	330	mW
			<u>[1]</u>	-	390	mW
		T <sub>sp</sub> = 25 °C		-	1090	mW
Per devic	e					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-d	rain diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-170	mA
ESD max	imum rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	1000	V

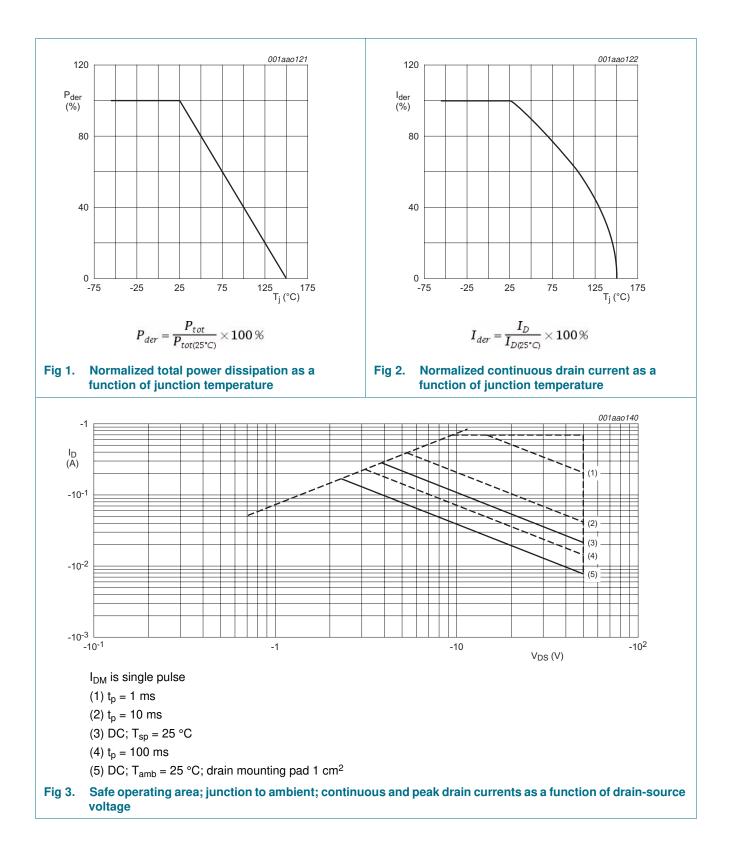
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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Product data sheet

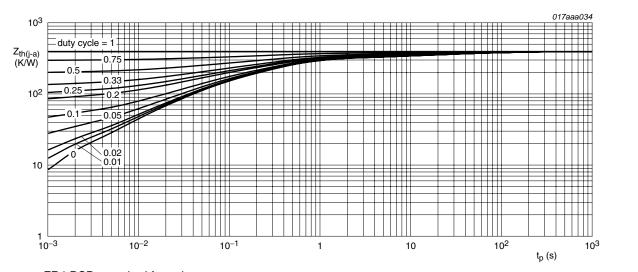
### 6. Thermal characteristics

	nermai characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	250	K/W
Per transisto	or						
R <sub>th(j-a)</sub>	thermal resistance from junction to	in free air	[1]	-	330	380	K/W
	ambient		[2]	-	280	320	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solde point	er		-	-	115	K/W

#### Table 6. Thermal characteristics

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

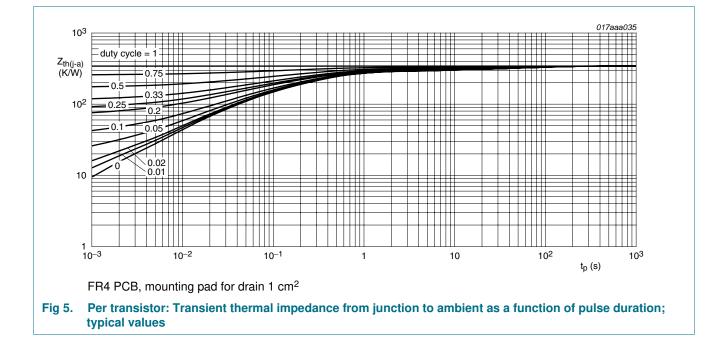


FR4 PCB, standard footprint

Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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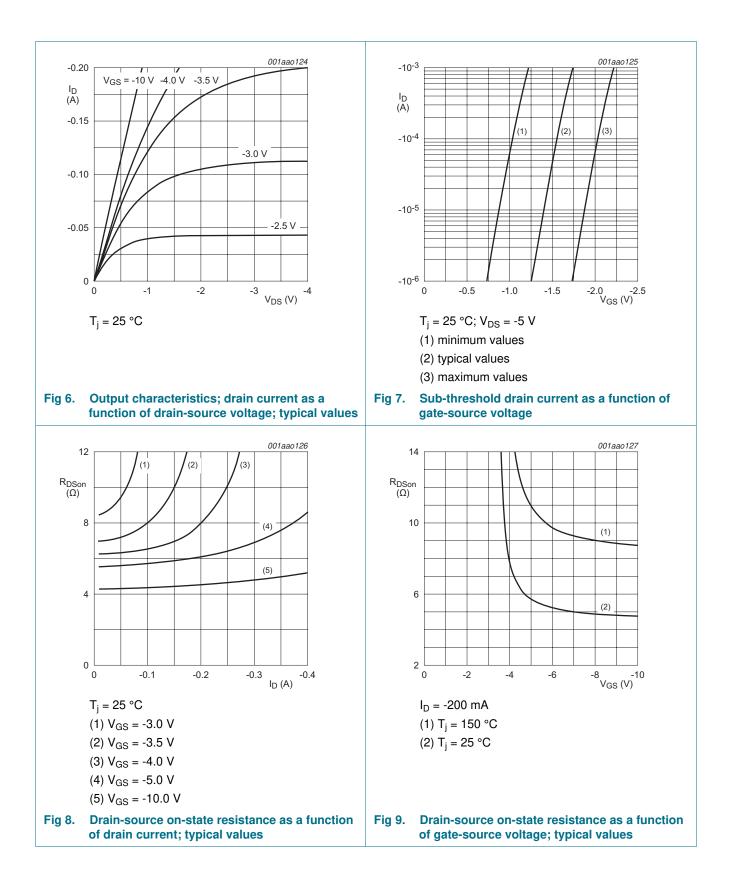


### 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	racteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -10 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	-50	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = -250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^\circ\text{C}$	-1.1	-1.6	-2.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-2	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -10 V; $I_D$ = -100 mA; $T_j$ = 25 °C	-	4.5	7.5	Ω
	resistance	$V_{GS}$ = -10 V; $I_{D}$ = -100 mA; $T_{j}$ = 150 °C	-	8	13.5	Ω
		$V_{GS}$ = -5 V; $I_D$ = -100 mA; $T_j$ = 25 °C	-	5.7	8.5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -100 mA; $T_{j}$ = 25 °C	-	150	-	mS
Dynamic of	characteristics (per transistor	r)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -25 V; $I_{D}$ = -200 mA; $V_{GS}$ = -5 V;	-	0.26	0.35	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \ ^{\circ}C$	-	0.12	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.09	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -25 V$ ; f = 1 MHz; $V_{GS} = 0 V$ ;	-	24	36	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \ ^{\circ}C$	-	4.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}=-30~V;~R_L=250~\Omega;~V_{GS}=-10~V;$	-	13	26	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	48	96	ns
t <sub>f</sub>	fall time		-	25	-	ns
Source-dr	ain diode (per transistor)					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-0.48	-0.85	-1.2	V

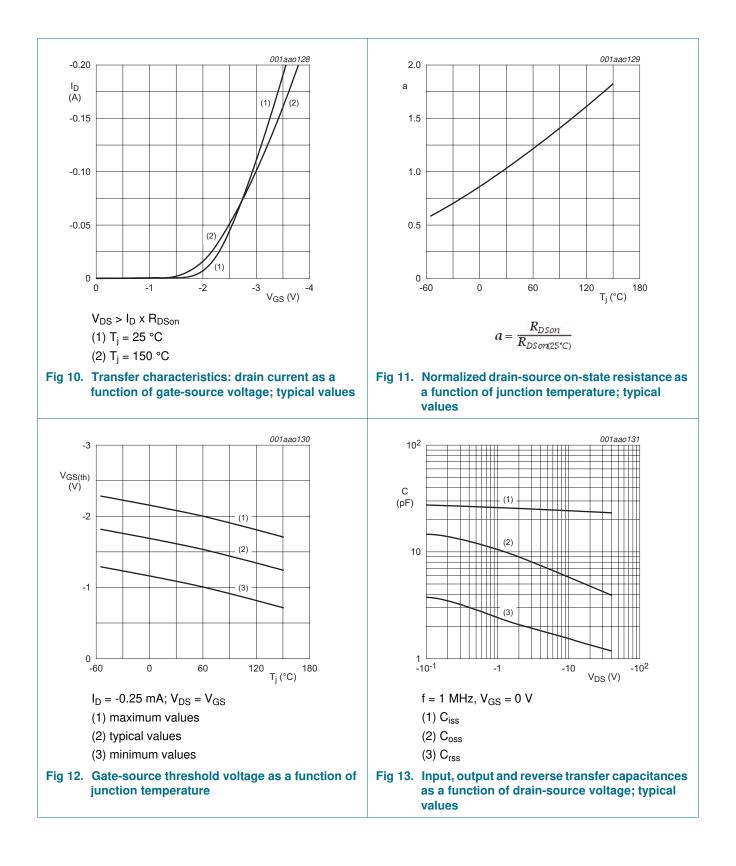
# **BSS84AKV**

#### 50 V, 170 mA dual P-channel Trench MOSFET



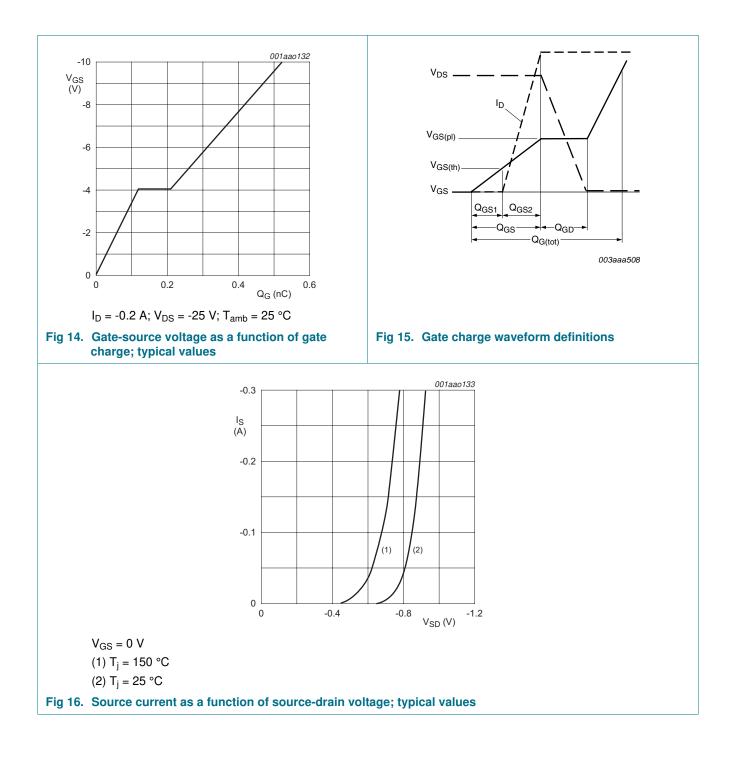
# **BSS84AKV**

### 50 V, 170 mA dual P-channel Trench MOSFET



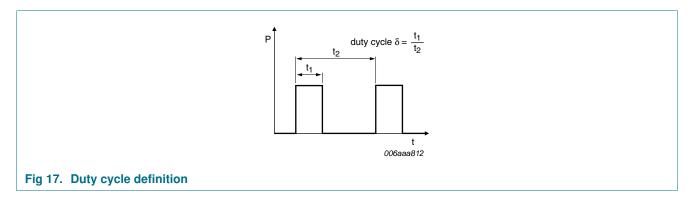
# **BSS84AKV**

#### 50 V, 170 mA dual P-channel Trench MOSFET



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### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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### 9. Package outline

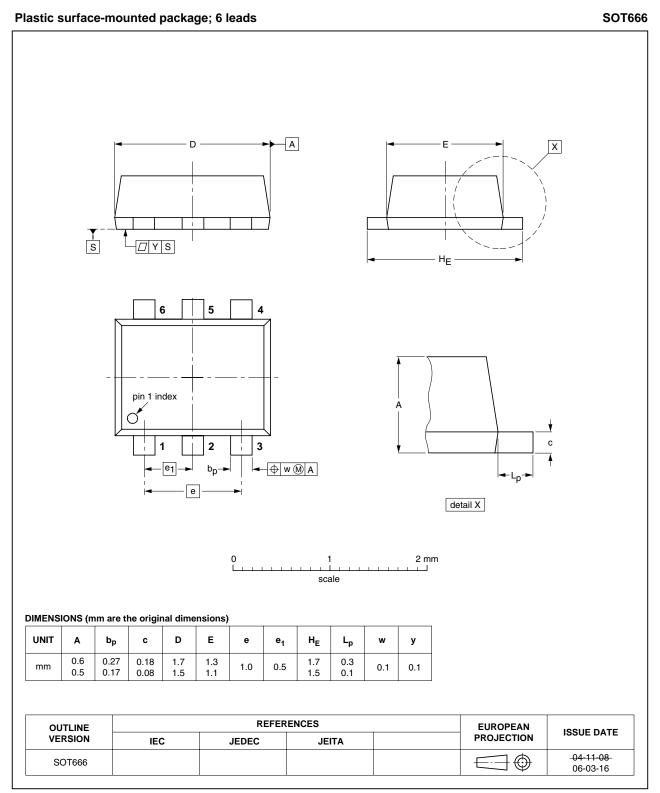
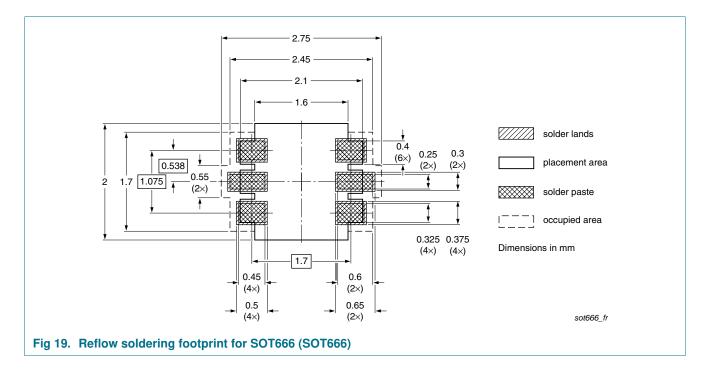


Fig 18. Package outline SOT666 (SOT666)

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### 10. Soldering



## **11. Revision history**

Table 8.	Revision hi	story			
Document	ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKV	v.1	20110519	Product data sheet	-	-

### 12. Legal information

### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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